

HiPerFET™ Power MOSFETs

ISOPLUS247™

F-Class: MegaHertz Switching

(Electrically Isolated Back Surface)

N-Channel Enhancement Mode

Avalanche Rated, High dV/dt

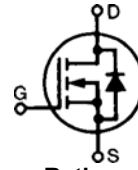
Low Gate Charge and Capacitances

Preliminary Data Sheet

IXFR 12N100F

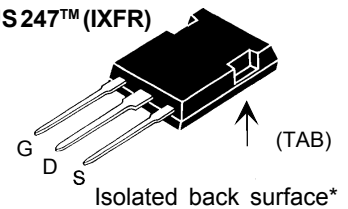
IXFR 10N100F

V_{DSS}	I_{D25}	$R_{DS(on)}$
1000 V	10 A	1.05 Ω
1000 V	9 A	1.20 Ω
$t_{rr} \leq 250$ ns		



Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1000		V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1$ M Ω	1000		V
V_{GS}	Continuous	± 20		V
V_{GSM}	Transient	± 30		V
I_{D25}	$T_C = 25^\circ\text{C}$	12N100	10	A
		10N100	9	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse width limited by T_{JM}	12N100	48	A
		10N100	40	A
I_{AR}	$T_C = 25^\circ\text{C}$	12N100	12	A
		10N100	10	A
E_{AR}	$T_C = 25^\circ\text{C}$	31		mJ
E_{AS}	$T_C = 25^\circ\text{C}$	1		J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100$ A/ μs , $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$, $R_G = 2$ Ω	5		V/ns
P_D	$T_C = 25^\circ\text{C}$	250		W
T_J		-40 ... +150		$^\circ\text{C}$
T_{JM}		150		$^\circ\text{C}$
T_{stg}		-40 ... +150		$^\circ\text{C}$
T_L	1.6 mm (0.063 in.) from case for 10 s	300		$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $t = 1$ min	2500		V~
Weight		5		g

ISOPLUS247™ (IXFR)



G = Gate
S = Source

D = Drain
TAB = Drain

Features

- RF capable MOSFETs
- Double metal process for low gate resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- easy to drive and to protect
- Fast intrinsic rectifier

Applications

- DC-DC converters
- Switched-mode and resonant-mode power supplies, >500kHz switching
- DC choppers
- 13.5 MHz industrial applications
- Pulse generation
- Laser drivers
- RF amplifiers

Advantages

- ISOPLUS 247™ package for clip or spring mounting
- Space savings
- High power density

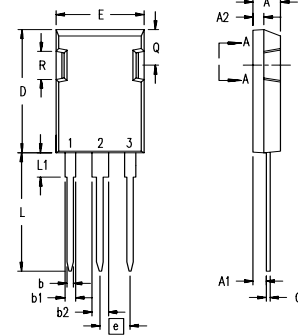
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0$ V, $I_D = 1$ mA	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4$ mA	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 20$ V, $V_{DS} = 0$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0$ V			50 μA 1.5 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = I_T$ Notes 1 & 2	12N100 10N100		1.05 Ω 1.2 Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = I_T$ Note 1	8	12	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		2700	pF
C_{oss}			305	pF
C_{rss}			93	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$ $R_G = 2\ \Omega$ (External)		12	ns
t_r			9.8	ns
$t_{d(off)}$			31	ns
t_f			12	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$		77	nC
Q_{gs}			16	nC
Q_{gd}			42	nC
R_{thJC}			0.50	K/W
R_{thCK}		0.15		K/W

Source-Drain Diode		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			12 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			48 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Note 1			1.5 V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$			250 ns
Q_{RM}		0.8		μC
I_{RM}		7		A

Note: 1. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$
 2. I_T test current: IXFR10N100 $I_T = 5\text{ A}$
 IXFR12N100 $I_T = 6\text{ A}$

PLUS 247™ Outline



Terminals: 1 - Gate
 2 - Drain (Collector)
 3 - Source (Emitter)
 4 - Drain (Collector)

Dim.	Millimeter Min. Max.	Inches Min. Max.
A	4.83 5.21	.190 .205
A ₁	2.29 2.54	.090 .100
A ₂	1.91 2.16	.075 .085
b	1.14 1.40	.045 .055
b ₁	1.91 2.13	.075 .084
b ₂	2.92 3.12	.115 .123
C	0.61 0.80	.024 .031
D	20.80 21.34	.819 .840
E	15.75 16.13	.620 .635
e	5.45 BSC	.215 BSC
L	19.81 20.32	.780 .800
L1	3.81 4.32	.150 .170
Q	5.59 6.20	.220 0.244
R	4.32 4.83	.170 .190